



09/943,190

CGJ
AJ

Docket No.: M4065.0698/P698
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:
Kristy A. Campbell et al.

Patent No.: 6,881,623

Issued: April 19, 2005

For: METHOD OF FORMING
CHALCOGENIDE COMPRISING
DEVICES, METHOD OF FORMING A
PROGRAMMABLE MEMORY CELL OF
MEMORY CIRCUITRY, AND A
CHALCOGENIDE COMPRISING DEVICE

**REQUEST TO CORRECT A CERTIFICATE OF CORRECTION PURSUANT
TO 37 CFR 1.322**

MS Post Issue
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

**Certificate
JUL 29 2005
of Correction**

Dear Sir:

Upon reviewing the attached Certificate of Correction for the above-identified patent, Patentees noted typographical errors which were not corrected. On pages 2 and 7, column 2 of the Patent, the following corrections, listed on the original Request for Correction (copy attached) were not completed.

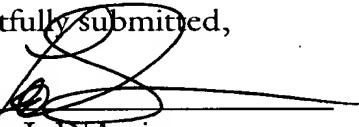
“Kluge, et al., “Silver photodifusion in amorphous Ge_xSe_{100-x} ”, Journal of Non-Crystalline Solids 124 (1990) pp. 180-183” should read --Kluge, et al., “Silver photodiffusion in amorphous Ge_xSe_{100-x} ”, Journal of Non-Crystalline Solids 124 (1990) pp. 186-193--.

“West et al., *Equivalent Circuit Modeling of the Ag|As_{0.24}S_{0.24}Ag₄₀|Ag System Prepared by Photodissolution of Ag*, 145 J. Electrochem. Soc., No. 9, pp. 2971-2974 (Sep. 1998)” should read --West et al., *Equivalent Circuit Modeling of the Ag|As_{0.24}S_{0.36}Ag₄₀|Ag System Prepared by Photodissolution of Ag*, 145 J. Electrochem. Soc., No. 9, pp. 2971-2974 (Sep. 1998)--.

Transmitted herewith is a proposed Certificate of Correction effecting such amendments. Patentees respectfully solicit the granting of the requested corrected Certificate of Correction and believe no fee is involved.

Dated: July 25, 2005

Respectfully submitted,

By 
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**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**Page 1 of 1

PATENT NO. : 6,881,623
APPLICATION NO. : 09/943,190
ISSUE DATE : April 19, 2005
INVENTOR(S) : Kristy A. Campbell et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On page 2, column 2, please correct the following:

"Kluge, et al., "Silver photodifusion in amorphous Ge_xSe_{100-x} ", Journal of Non-Crystalline Solids 124 (1990) pp. 180-183" should read --Kluge, et al., "Silver photodiffusion in amorphous Ge_xSe_{100-x} ", Journal of Non-Crystalline Solids 124 (1990) pp. 186-193--.

On page 7, column 2, please correct the following:

"West et al., *Equivalent Circuit Modeling of the $Ag|As_{0.24}S_{0.24}Ag_{a40}|Ag$ System Prepared by Photodissolution of Ag*, 145 J. Electrochem. Soc., No. 9, pp. 2971-2974 (Sep. 1998)" should read --West et al., *Equivalent Circuit Modeling of the $Ag|As_{0.24}S_{0.36}Ag_{a40}|Ag$ System Prepared by Photodissolution of Ag*, 145 J. Electrochem. Soc., No. 9, pp. 2971-2974 (Sep. 1998)--.

MAILING ADDRESS OF SENDER (Please do not use customer number below):

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UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,881,623 B2
DATED : April 19, 2005
INVENTOR(S) : Kristy A. Campbell et al.

Page 1 of 2

COPY

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page.

Item [56], **References Cited, OTHER PUBLICATIONS**, please correct the following:

"D.B. Johnson, et al., "Lateral Diffusion in Ag-Be Thin-Film Couples", Journal of Applied Physics, Vol. 40, No. 1, Jan. 1963, pp. 149-152" should read -- D.B. Johnson, et al., "Lateral Diffusion in Ag-Se Thin-Film Couples", Journal of Applied Physics, Vol. 40, No. 1, January 1969, pp. 149-152 --.

"U.S. Appl. No. 09/778,963, filed Feb. 8, 2001, Moore" should read -- U.S. Appl. No. 09/779,983, filed Feb. 8, 2001, Moore --.

The following two items should be inserted:

-- U.S. Appl. No. 10/077,867, filed Feb. 20, 2002, Campbell et al.

U.S. Appl. No. 10/232,757, filed Aug. 29, 2002, Li et al. --.

Please correct the following:

"Hirose, et al., "High Memory Behavior and Reliability in Amorphous As₁S₀ Film Doped with Ag", Jul. 17, 1980, pp. K187-K190" should read -- Hirose, et al., "High Speed Memory Behavior and Reliability of an Amorphous As₂S₃ Film Doped with Ag", Jul. 17, 1980, pp. K187-K190 --.

"Hirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As₁B₁ films", Journal of Applied Physics, vol. 47, No. 6, Jun. 1976, pp. 2787-2772" should read -- Hirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As₂S₃ films", Journal of applied Physics, Vol. 47, No. 6. Jun. 1976, pp. 2767-2772 --.

"Kluge, et al., "Silver photodiffusion in amorphous Ga₁Se₁", Journal of Non-Crystalline Solids 124 (1990) pp. 180-183" should read -- Kluge, et al., "Silver photodiffusion in amorphous Ge_xSe_{100-x}", Journal of Non-Crystalline Solids 124 (1990) pp. 186-193 --.

"Aron Technologies Corporation, Technology Description: *Programmable Metallization Cell (PMC)*, (pre-Jul. 7, 2000) pp. 1-5" should read -- Axon Technologies Corporation, Technology Description: *Programmable Metallization Cell (PMC)*, (pre-Jul. 7, 2000) pp. 1-6 --.

"Huggett et al., *Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF₆*, 42 Appl. Phys. Lett., No. 7, pp. 592-594 (Apr. 1983)" should read -- Huggett et al., *Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF₆*, 42 Appl. Phys. Lett., No. 7, pp. 592-594 (Apr. 1983) --.

AUG 03 2005

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,881,623 B2
DATED : April 19, 2005
INVENTOR(S) : Kristy A. Campbell et al.

Page 2 of 2

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COF

Title page (cont'd).

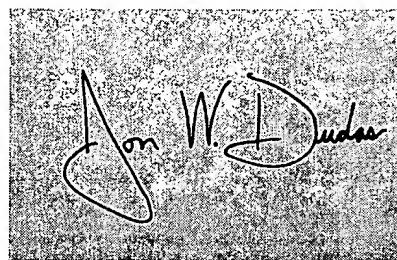
please correct the following:

"West et al., *Equivalent Circuit Modeling of the Ag₁As_{0.24}S_{0.24}Ag_{0.40}Ag System Prepared by Photodissolution of Ag*, 145 J. Electrochem. Soc., No. 9, pp. 2971-2974 (Sep. 1998)" should read -- West et al., *Equivalent Circuit Modeling of the Ag₁As_{0.24}S_{0.24}Ag_{0.40}Ag System Prepared by Photodissolution of Ag*, 145 J. Electrochem. Soc., No. 9, pp. 2971-2974 (Sep. 1998) --.



Signed and Sealed this

Twenty-eighth Day of June, 2005



JON W. DUDAS
Director of the United States Patent and Trademark Office

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"Hirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As_1B_1 films", Journal of Applied Physics, vol. 47, No. 6, Jun. 1976, pp. 2787-2772" should read --Hirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As_2S_3 films", Journal of applied Physics, Vol. 47, No. 6, Jun. 1976, pp. 2767-2772--.

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The errors were not in the application as filed by applicants or in the IDS's filed (copies attached); accordingly no fee is required.